



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

TO-92 Plastic-Encapsulate Transistors

2N5401 TRANSISTOR (PNP)

FEATURE

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

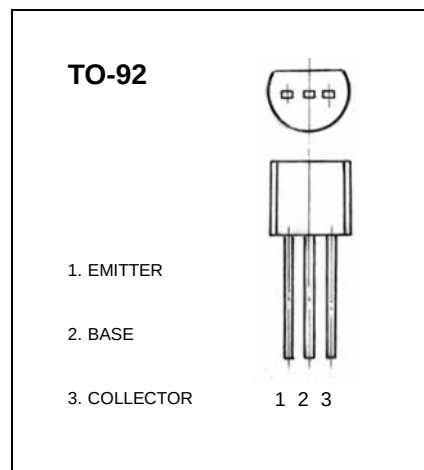
I_{CM} : -0.6 A

Collector-base voltage

$V_{(BR)CBO}$: -160 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 mA, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -120 V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5 V, I_C = -1 mA$	80			
	$h_{FE(2)}$	$V_{CE} = -5 V, I_C = -10 mA$	80		250	
	$h_{FE(3)}$	$V_{CE} = -5 V, I_C = -50 mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50 mA, I_B = -5 mA$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50 mA, I_B = -5 mA$			-1	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$ $f = 30MHz$	100			MHz

CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B	C
Range	80-160	120-180	150-250